

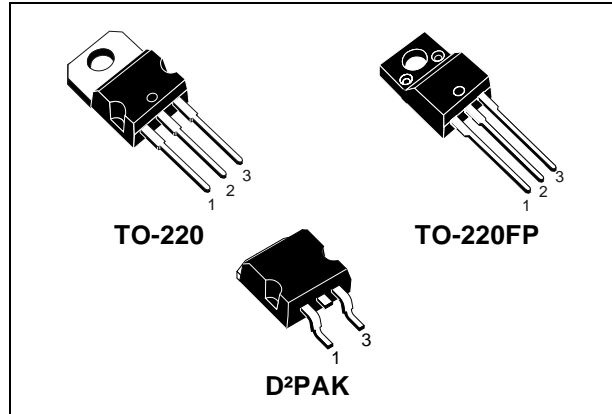


# STGP7NB60KD - STGB7NB60KD STGP7NB60KDFP

N-CHANNEL 7A - 600V - TO-220/TO-220FP/D<sup>2</sup>PAK  
SHORT CIRCUIT RATED PowerMESH™ IGBT

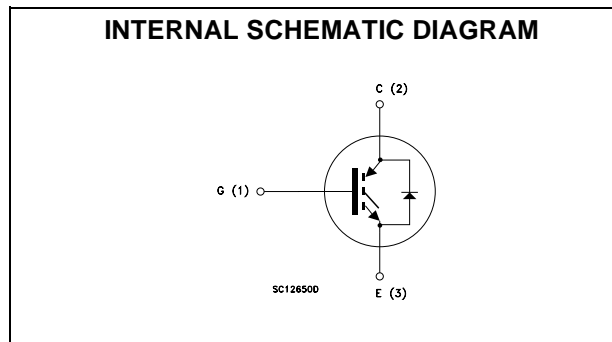
TYPE	V <sub>CES</sub>	V <sub>CE(sat)</sub>	I <sub>C</sub>
STGP7NB60KD	600 V	< 2.8 V	7 A
STGP7NB60KDFP	600 V	< 2.8 V	7 A
STGB7NB60KD	600 V	< 2.8 V	7 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V<sub>cesat</sub>)
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT
- HIGH FREQUENCY OPERATION
- SHORT CIRCUIT RATED
- CO-PACKAGED WITH TURBOSWITCH™ ANTIPARALLEL DIODE



## DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency motor control applications with short circuit withstand capability.



## APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS AND PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES

## ORDER CODES

PART NUMBER	MARKING	PACKAGE	PACKAGING
STGP7NB60KD	GP7NB60KD	TO-220	TUBE
STGB7NB60KDT4	GB7NB60KD	D <sup>2</sup> PAK	TAPE & REEL
STGP7NB60KDFP	GP7NB60KDFP	TO-220FP	TUBE

## STGP7NB60KD - STGP7NB60KDFP - STGB7NB60KD

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STGP7NB60KD STGB7NB60KD	STGP7NB60KDFP	
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>GS</sub> = 0)	600		V
V <sub>ECR</sub>	Emitter-Collector Voltage	20		V
V <sub>GE</sub>	Gate-Emitter Voltage	±20		V
I <sub>C</sub>	Collector Current (continuous) at T <sub>C</sub> = 25°C	14		A
I <sub>C</sub>	Collector Current (continuous) at T <sub>C</sub> = 100°C	7		A
I <sub>CM</sub> (■)	Collector Current (pulsed)	56		A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	80	25	W
	Derating Factor	0.64	0.20	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage A.C.(t= 1 sec; T <sub>c</sub> = 25°C)	--	2500	V
T <sub>stg</sub>	Storage Temperature	-55 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(■) Pulse width limited by safe operating area

### THERMAL DATA

		TO-220 D <sup>2</sup> PAK	TO-220FP	
R <sub>thj-case</sub>	Thermal Resistance Junction-case Max	1.56	5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient Max	62.5		°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>BR(CES)</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 250 μA, V <sub>GE</sub> = 0	600			V
I <sub>CES</sub>	Collector cut-off (V <sub>GE</sub> = 0)	V <sub>CE</sub> = Max Rating, T <sub>C</sub> = 25°C V <sub>CE</sub> = Max Rating, T <sub>C</sub> = 125°C			50 500	μA μA
I <sub>GES</sub>	Gate-Emitter Leakage Current (V <sub>CE</sub> = 0)	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GE(th)</sub>	Gate Threshold Voltage	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA	5		7	V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15V, I <sub>C</sub> = 7 A V <sub>GE</sub> = 15V, I <sub>C</sub> = 7 A, T <sub>j</sub> = 125°C		2.3 1.9	2.8	V V

## STGP7NB60KD - STGP7NB60KDFP - STGB7NB60KD

### ELECTRICAL CHARACTERISTICS (CONTINUED) DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$	Forward Transconductance	$V_{CE} = 15\text{ V}, I_C = 7\text{ A}$		3.7		S
$C_{ies}$ $C_{oes}$ $C_{res}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0$		495 77 13		pF pF pF
$Q_g$ $Q_{ge}$ $Q_{gc}$	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 480\text{ V}, I_C = 7\text{ A},$ $V_{GE} = 15\text{ V}$		32.7 5.9 18.3	45	nC nC nC
tscw	Short Circuit Withstand Time	$V_{ce} = 0.5 V_{BR(CES)}, V_{GE} = 15\text{ V}$ $T_j = 125^\circ\text{C}, R_G = 10\ \Omega$	10			$\mu\text{s}$

### SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 480\text{ V}, I_C = 7\text{ A}$		15		ns
$t_r$	Rise Time	$R_G = 10\ \Omega, V_{GE} = 15\text{ V}$		6		ns
$(di/dt)_{on}$ Eon	Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 480\text{ V}, I_C = 7\text{ A}, R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}, T_j = 125^\circ\text{C}$		980 95		A/ $\mu\text{s}$ $\mu\text{J}$

### SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_c$	Cross-over Time	$V_{CC} = 480\text{ V}, I_C = 7\text{ A},$ $R_{GE} = 10\ \Omega, V_{GE} = 15\text{ V}$		105		ns
$t_r(V_{off})$	Off Voltage Rise Time			30		ns
$t_{d(off)}$	Delay Time			50		ns
$t_f$	Fall Time			100		ns
$E_{off(**)}$	Turn-off Switching Loss			140		$\mu\text{J}$
$E_{ts}$	Total Switching Loss			200		$\mu\text{J}$
$t_c$	Cross-over Time	$V_{CC} = 480\text{ V}, I_C = 7\text{ A},$ $R_{GE} = 10\ \Omega, V_{GE} = 15\text{ V}$ $T_j = 125^\circ\text{C}$		227		ns
$t_r(V_{off})$	Off Voltage Rise Time			68		ns
$t_{d(off)}$	Delay Time			52		ns
$t_f$	Fall Time			150		ns
$E_{off(**)}$	Turn-off Switching Loss			300		$\mu\text{J}$
$E_{ts}$	Total Switching Loss			395		$\mu\text{J}$

(\*\*) Losses include Also the Tail (Jedec Standardization)

### COLLECTOR-EMITTER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_f$	Forward Current				7	A
$I_{fm}$	Forward Current pulsed				56	A
$V_f$	Forward On-Voltage	$I_f = 3.5\text{ A}$ $I_f = 3.5\text{ A}, T_j = 125^\circ\text{C}$		1.4 1.2	1.9	V V
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 7\text{ A}, V_R = 35\text{ V},$ $T_j = 125^\circ\text{C}, di/dt = 100\text{ A}/\mu\text{s}$		50 70 2.7		ns nC A

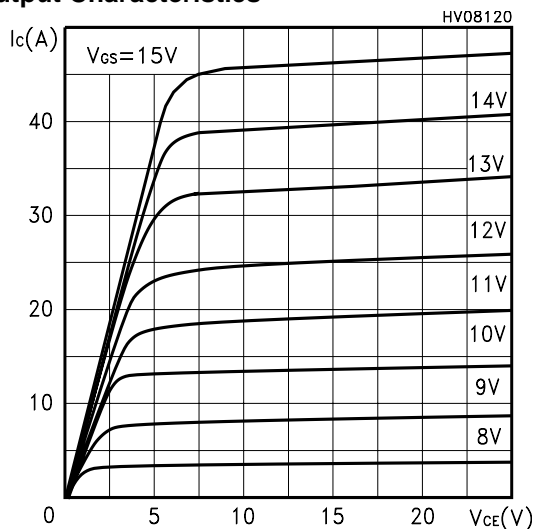
Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

2. Pulse width limited by max. junction temperature.

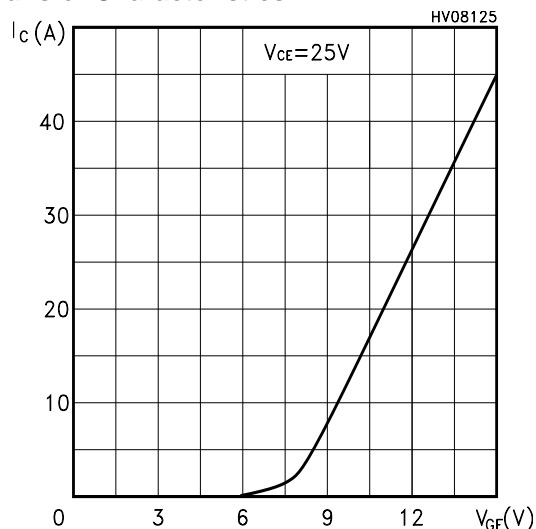
(\*\*) Losses include Also the Tail (Jedec Standardization)



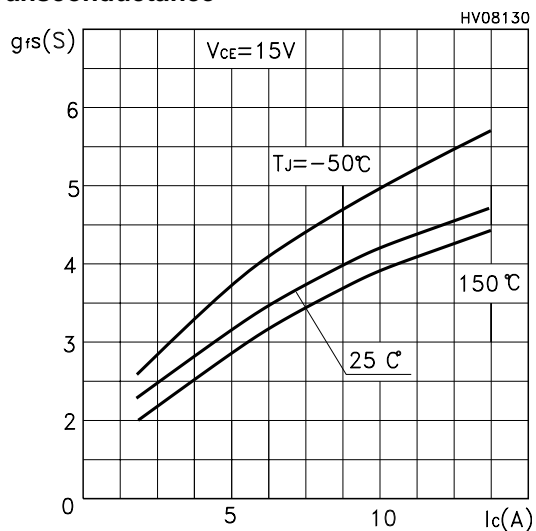
**Output Characteristics**



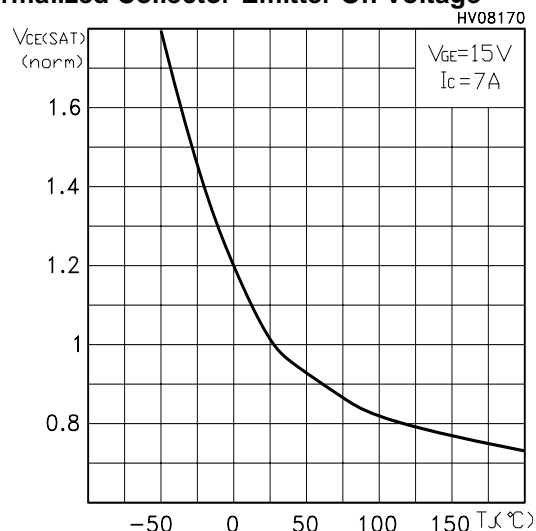
**Transfer Characteristics**



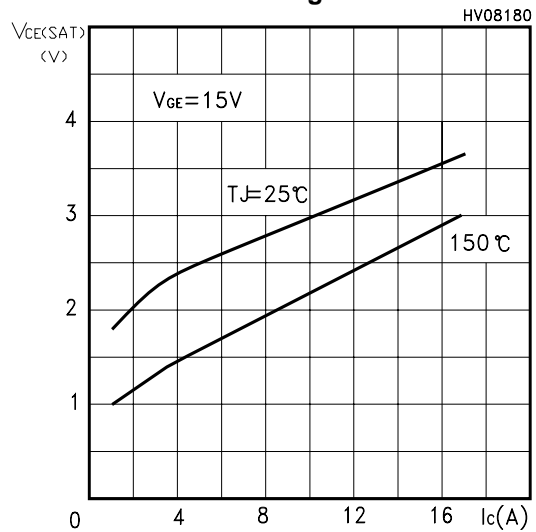
**Transconductance**



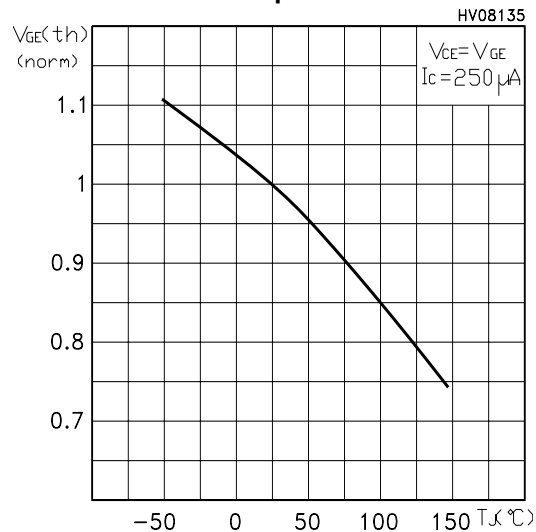
**Normalized Collector-Emitter On Voltage**



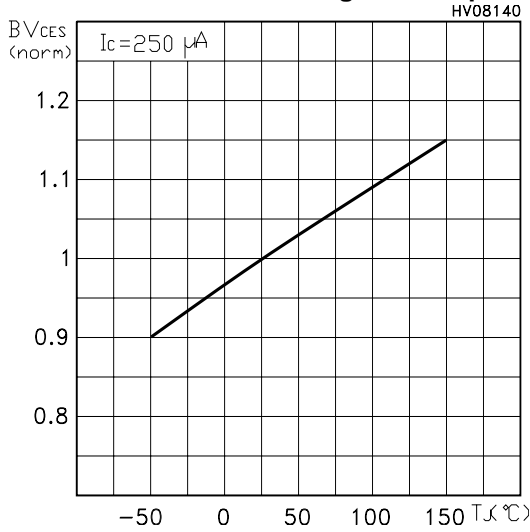
**Collector-Emitter On Voltage vs Collector Current**



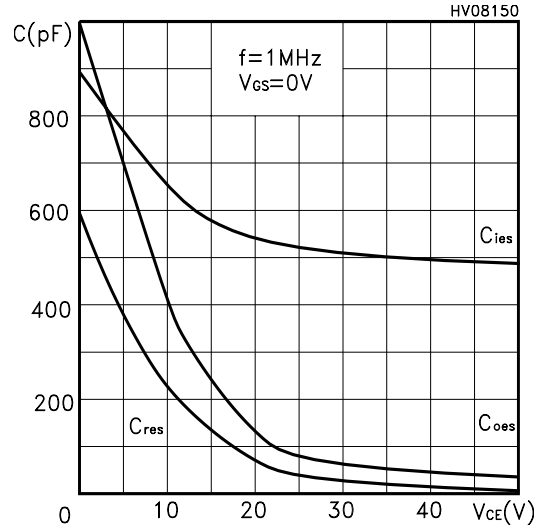
**Gate Threshold vs Temperature**



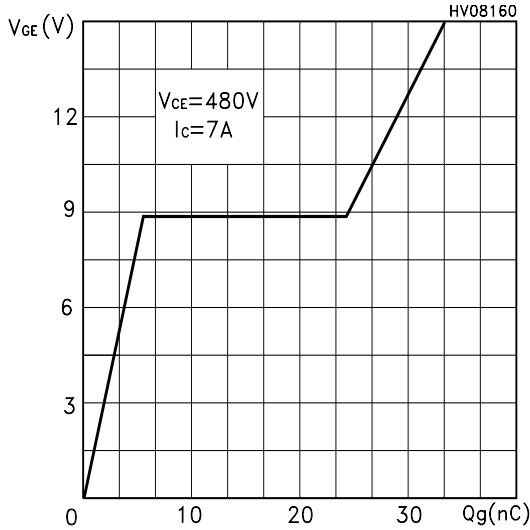
Normalized Breakdown Voltage vs Temperature



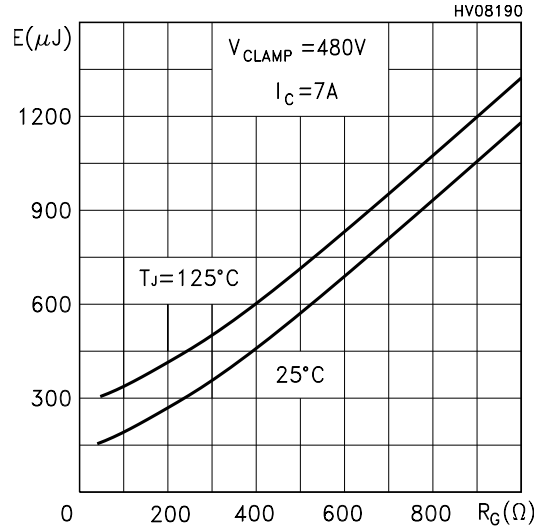
Capacitance Variations



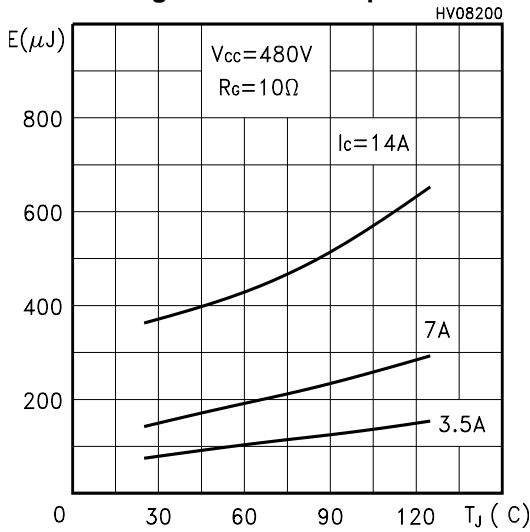
Gate Charge vs Gate-Emitter Voltage



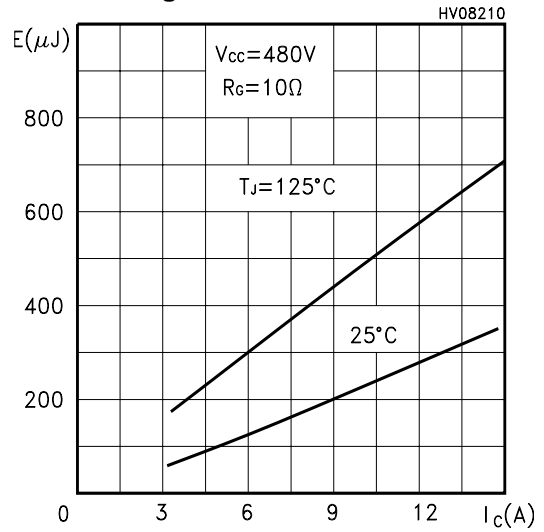
Total Switching Losses vs Gate Resistance



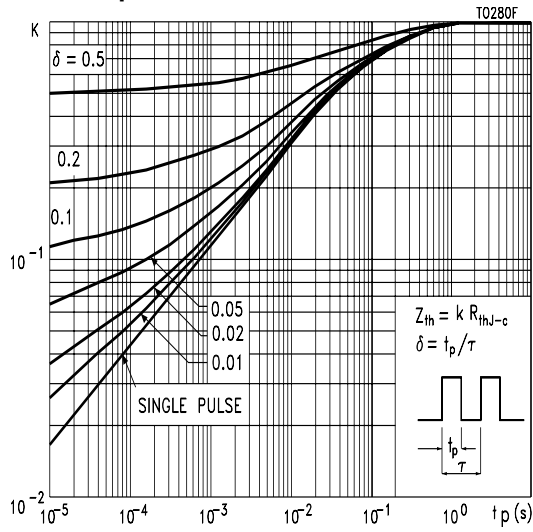
Total Switching Losses vs Temperature



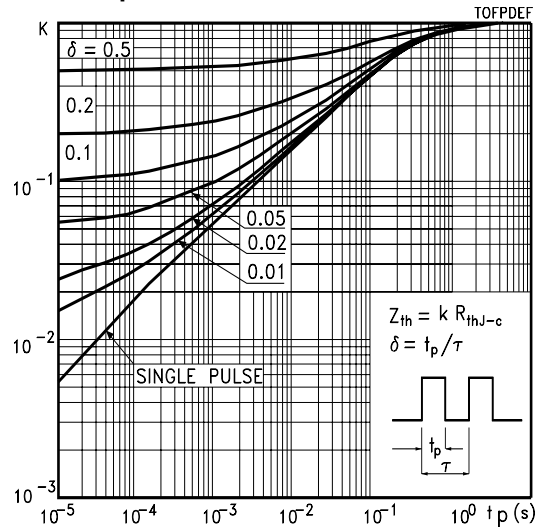
Total Switching Losses vs Collector Current



Thermal Impedance for TO-220/D<sup>2</sup>PAK



Thermal Impedance for TO-220FP



Turn-Off SOA

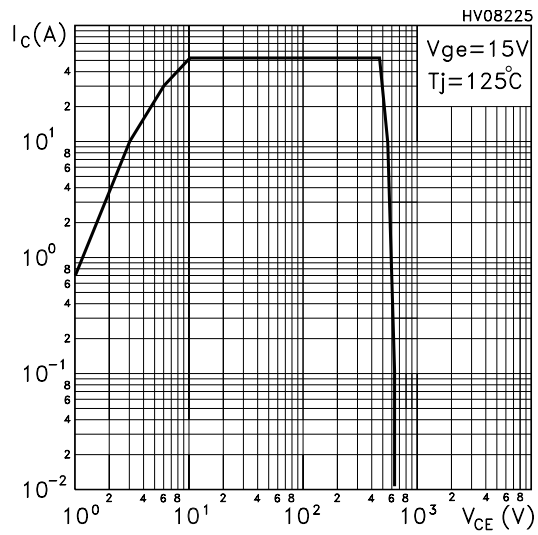


Fig. 1: Gate Charge test Circuit

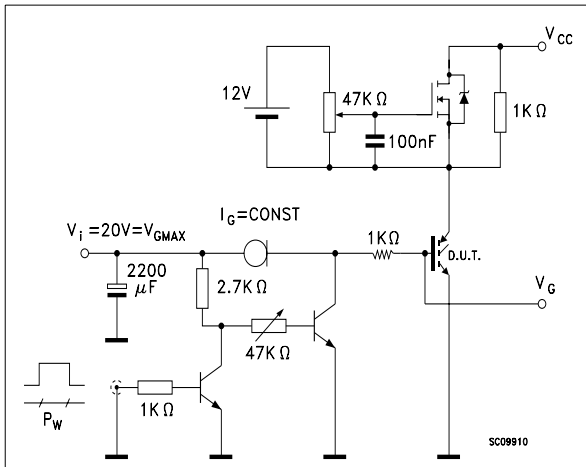
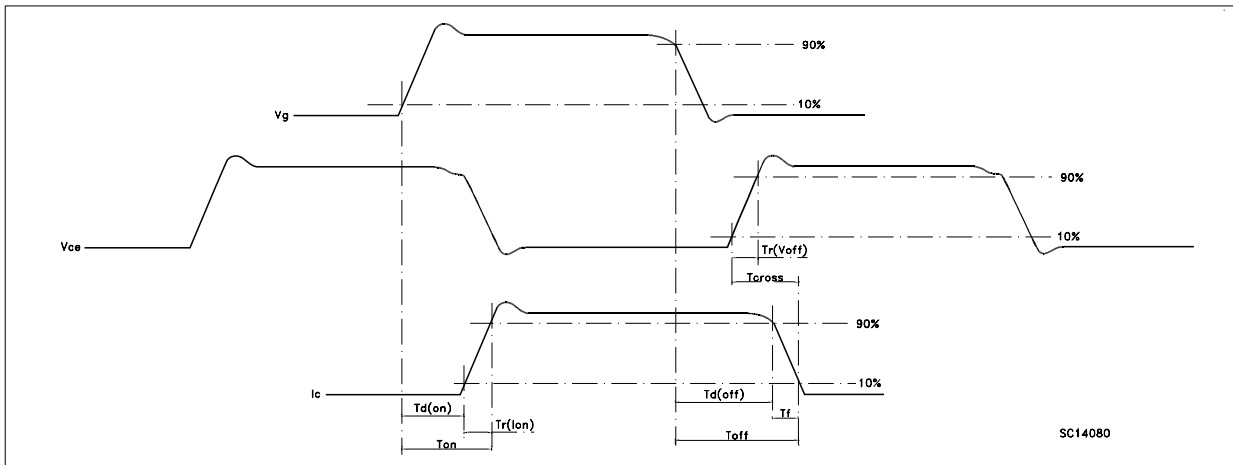
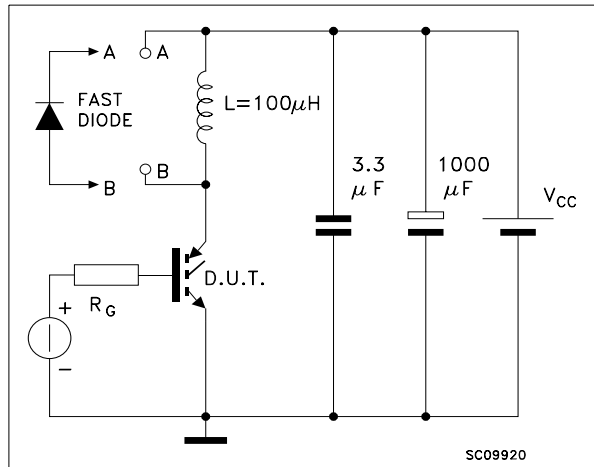
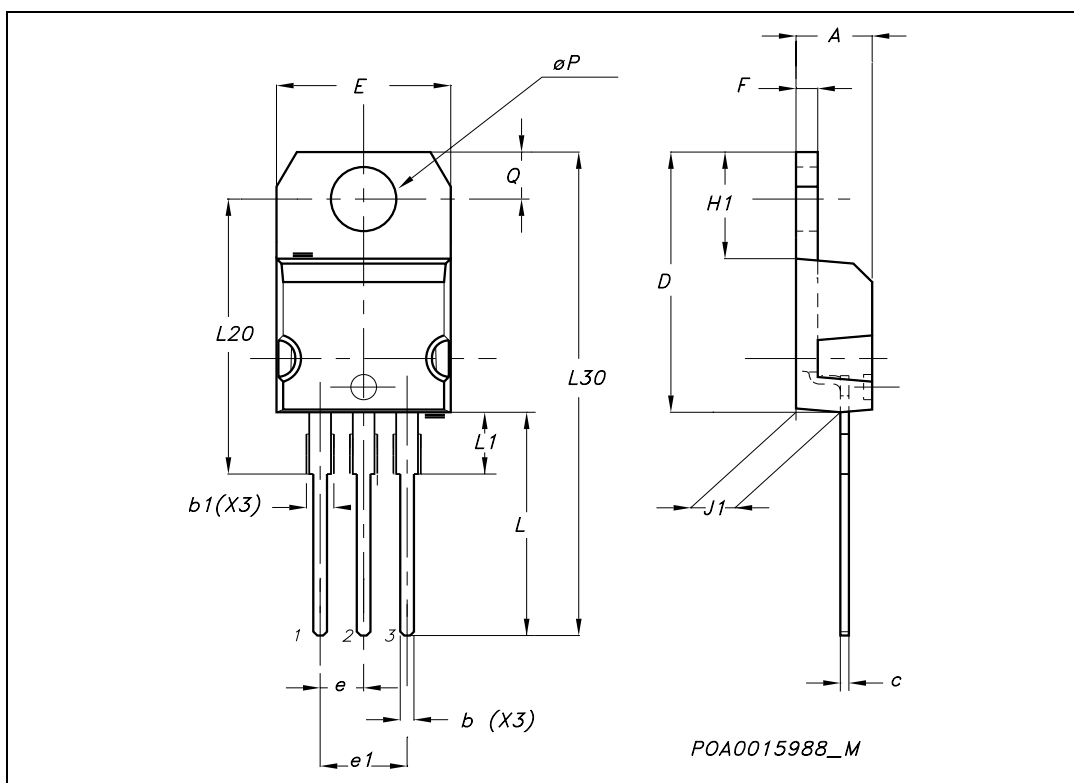


Fig. 2: Test Circuit For Inductive Load Switching



**TO-220 MECHANICAL DATA**

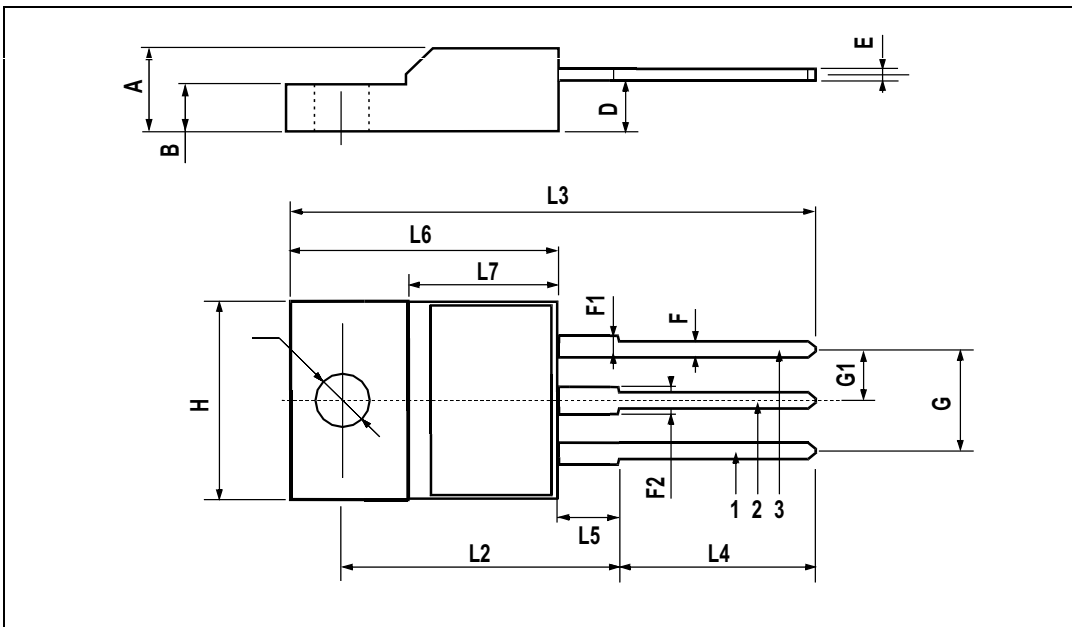
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116





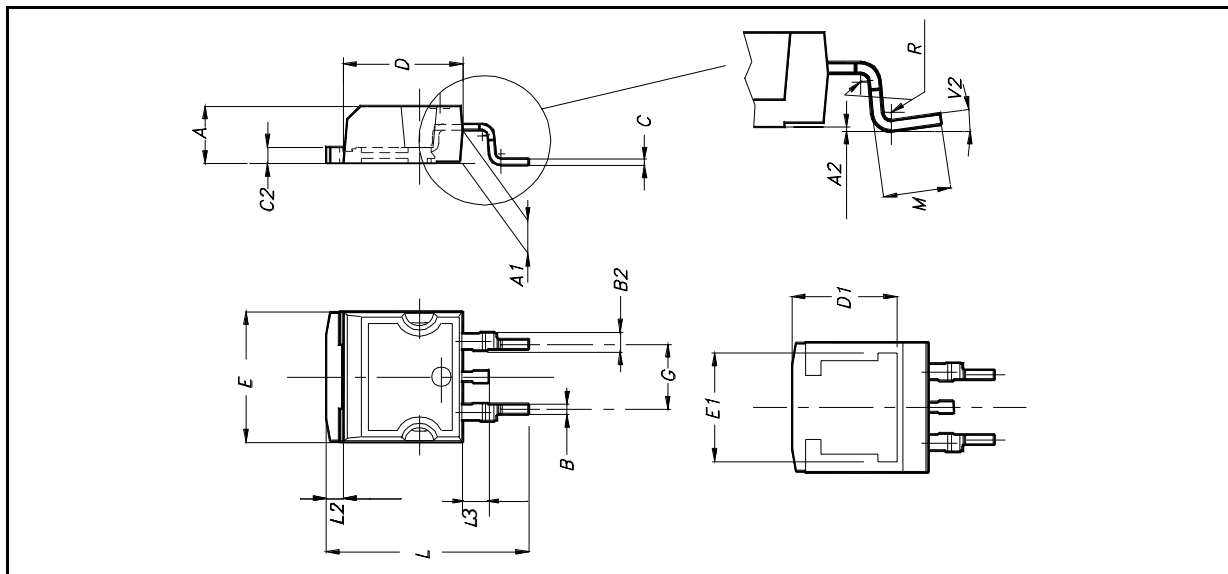
**TO-220FP MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			





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